

DO-41 Plastic-Encapsulate Diodes

Features

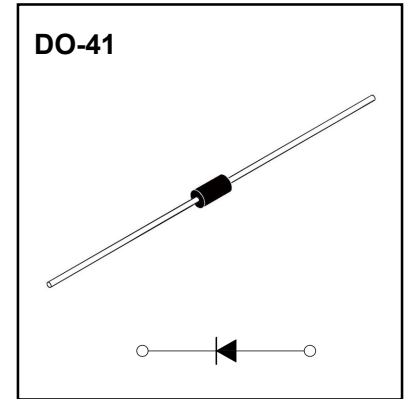
- $I_{F(AV)}$ 1A
- V_{RRM} 50V-1000V
- High surge current capability
- Polarity: Color band denotes cathode

Application

- Rectifier

Marking

- 1N400X
X : From 1 To 7



Limiting Values(Absolute Maximum Rating)

Item	Symbol	Unit	Test Conditions	1N40						
				01	02	03	04	05	06	07
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V		35	70	140	280	420	560	700
Maximum DC Blocking Voltage	V_{DC}	V		50	100	200	400	600	800	1000
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load, $T_a=75^\circ\text{C}$	1						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz Half-sine wave, 1 cycle, $T_a=25^\circ\text{C}$	30						
Junction Temperature	T_J	$^\circ\text{C}$		-55 ~ +150						
Storage Temperature	T_{STG}	$^\circ\text{C}$		-55 ~ +150						

Electrical Characteristics (T=25°C Unless otherwise specified)

Item	Symbol	Unit	Test Condition	Max	
Maximum Peak Forward Voltage	V_{FM}	V	$I_{FM}=1.0\text{A}$	1.1	
Maximum Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$	5
	I_{RRM2}			$T_a=100^\circ\text{C}$	50
Typical junction capacitance	C_J	pF	Measured at 1MHz and applied reverse voltage of 4.0V D.C.	15	
Typical Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C}/\text{W}$	Between junction and ambient	50	
	$R_{\theta J-L}$		Between junction and Lead	8	

Notes:

Thermal resistance from junction to ambient at 0.375" (9.5mm)lead length,P.C.B. mounted

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

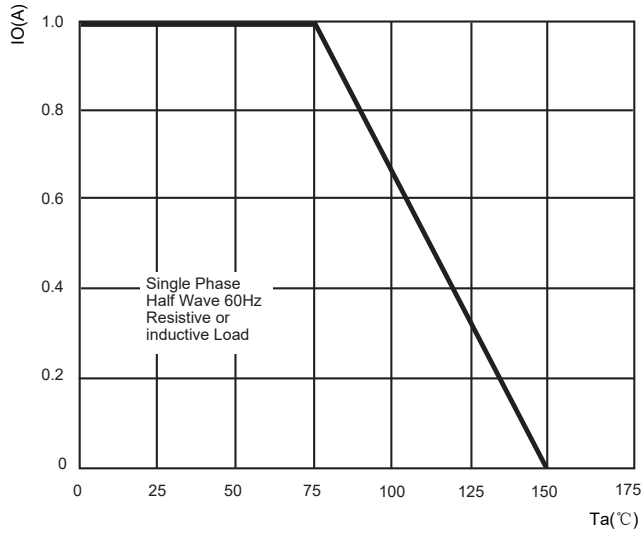


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

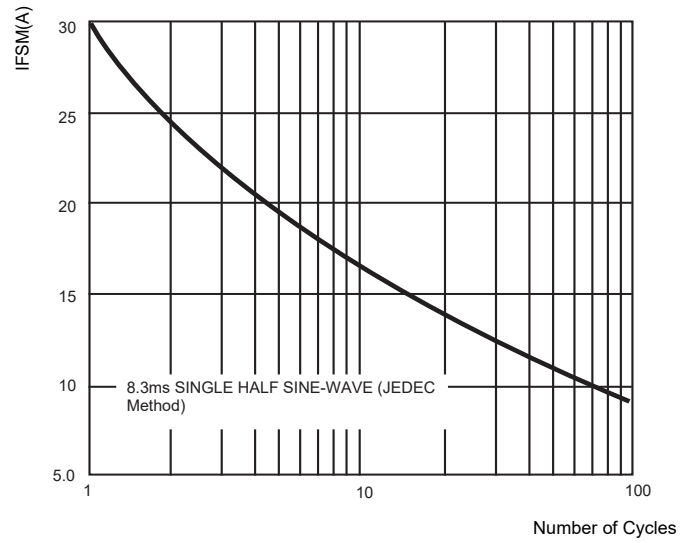


FIG.3: TYPICAL FORWARD CHARACTERISTICS

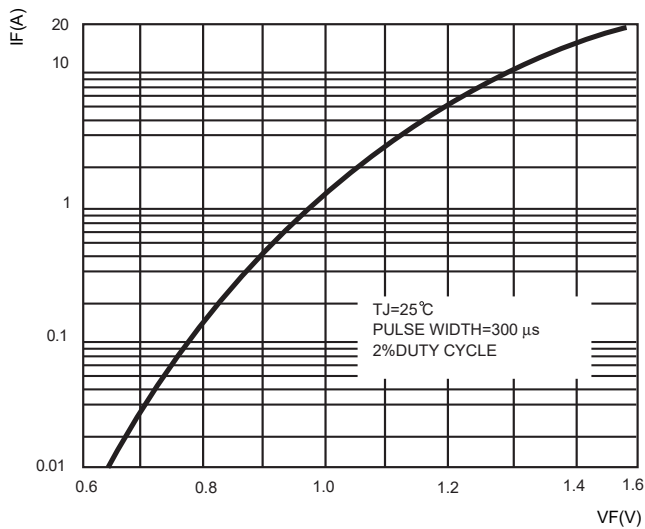
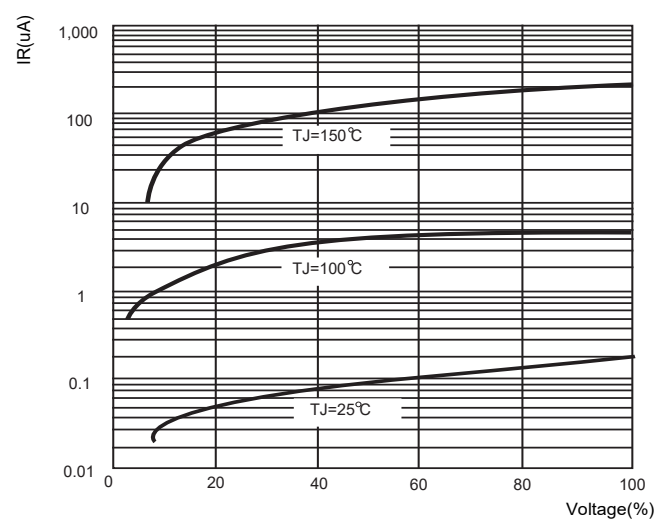
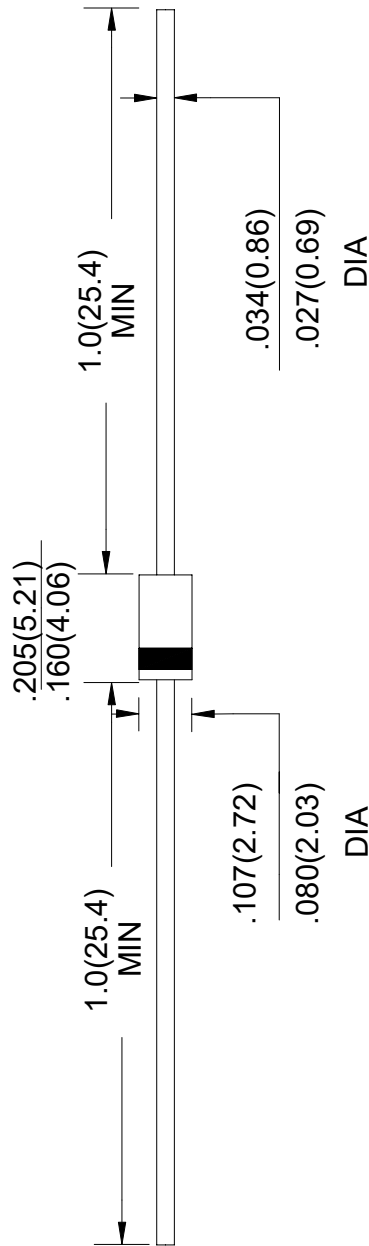


FIG.4: TYPICAL REVERSE CHARACTERISTICS





Unit: in inches (millimeters)